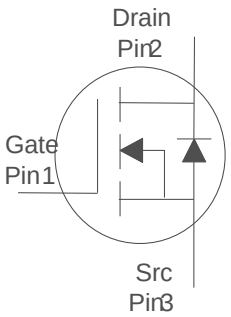
+ * : 1 6 /

120V N-Ch Power MOSFET

Feature

º High Speed Power Smooth Switching Logic(w)040T/wT-M346 Td 22/P <</MCID <</MCID 3Pin

V_{DSS}	120	V
$R_{DS(on),typ}$	5	m :
$I_{D\ (Sillicon\ Limited)}$	160	A
$I_{D\ (Package\ Limited)}$	120	A



Part Number	Package	Marking
+ * : 1 6 /	TO-262	: 1 6 /

Absolute Maximum Ratings at T_j X Q O H V V R W K H U Z L V H V S H F L I L H G

		Conditions	Value	Unit
	I_D		160	
		T_C	113	
Continuous Drain Current (Package Limited)		T_C	120	
Gate to Source Voltage	V_{GS}	-	±20	V
Pulsed Drain Current	I_{DM}	-	540	A
Avalanche Energy, Single Pulse	E_{AS}	L=0.4mH, T_C	720	mJ
Power Dissipation	P_D	T_C	333	:
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to175	

	a - &	0.45	:

Fig 1. Typical Output Characteristics

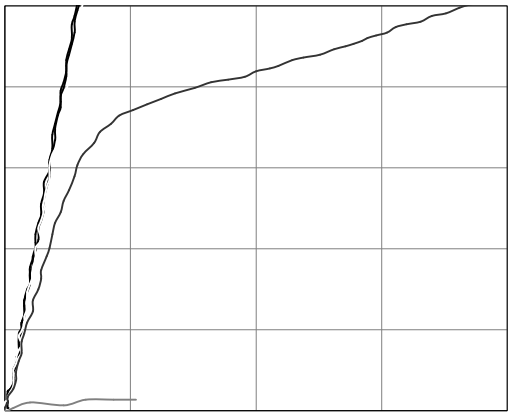


Figure 2. On-Resistance vs. Gate-Source Voltage

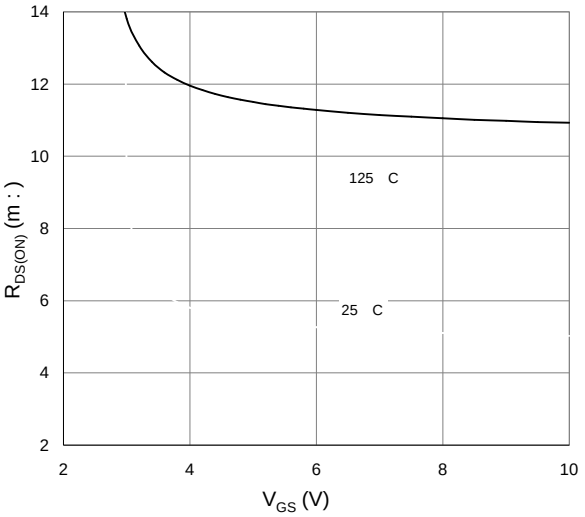
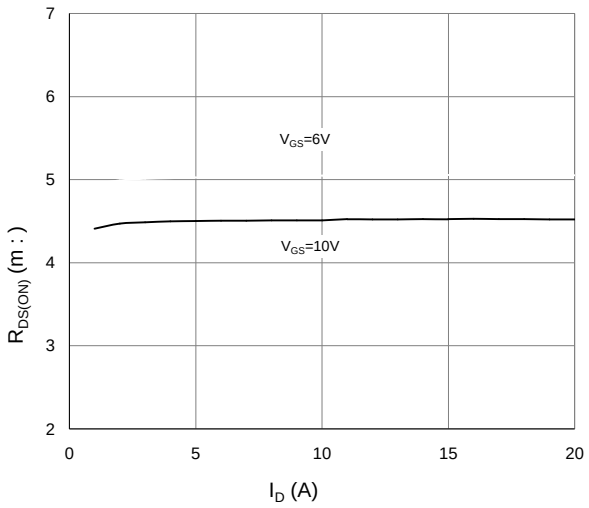
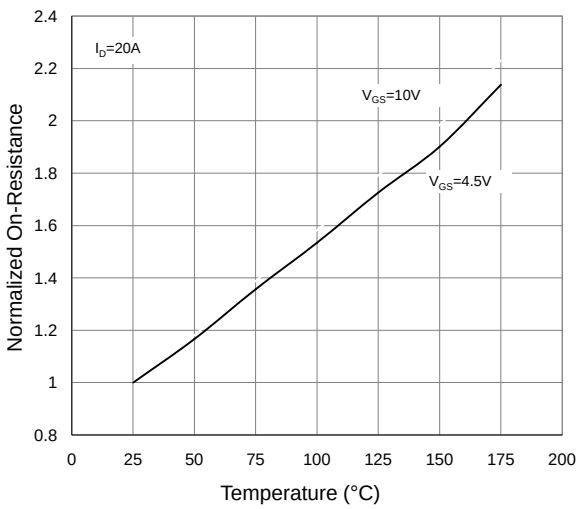


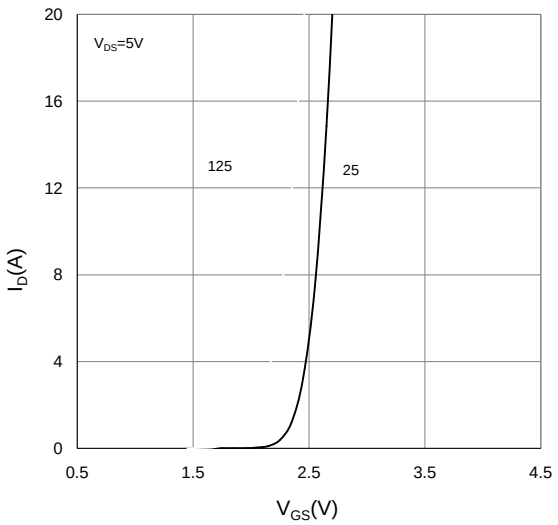
Figure 3. On-Resistance vs. Drain Current and Gate Voltage

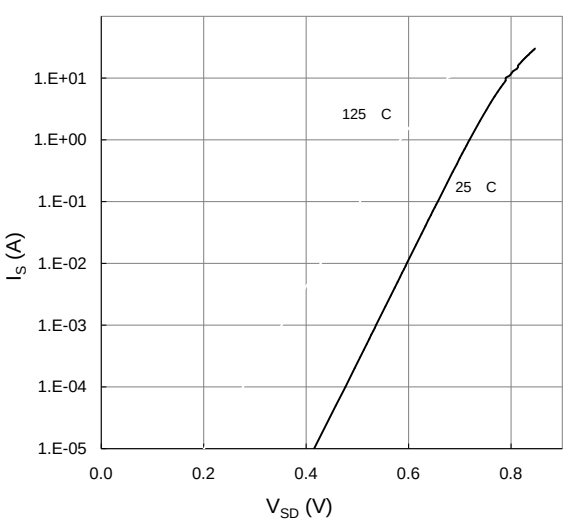


) L J X U H 1 R U P D O L] H G 2 Q 5 H V L V W D Q F H Y V - X Q F W L R Figure 5. Normalized On-Resistance vs. Junction Temperature



) L J X U H 7 \ S L F D O 7 U D Q V I H U & K D U D F W H U L V W L F V Figure 6. Typical Source-Drain Diode Forward Voltage





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